

# S3S Conference 2.5/3D Technology and Commercialization

October 11, 2016





# WHAT ARE THE DRIVERS OF CHANGE?



# Precipitating Events for Change

# FALLOUT FROM A FIRE: CHIP PRICES SOAR The Washington Post

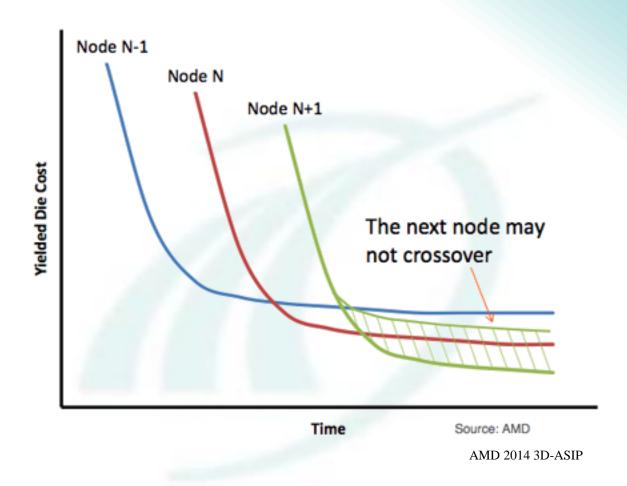
By John Mintz July 22, 1993

Prices on some computer memory chips have almost doubled in recent weeks, and one reason is an explosion at a Japanese plastics factory that makes a compound used in the chips. But some computer industry executives say the prices probably will drop as fast as they rose once alternative sources for the plastic are found.

The July 4 fire destroyed the Sumitomo Chemical Co. plant in Nihama, which supplies 60 percent of the epoxy resin used to manufacture DRAM -- dynamic random access memory -- computer chips.



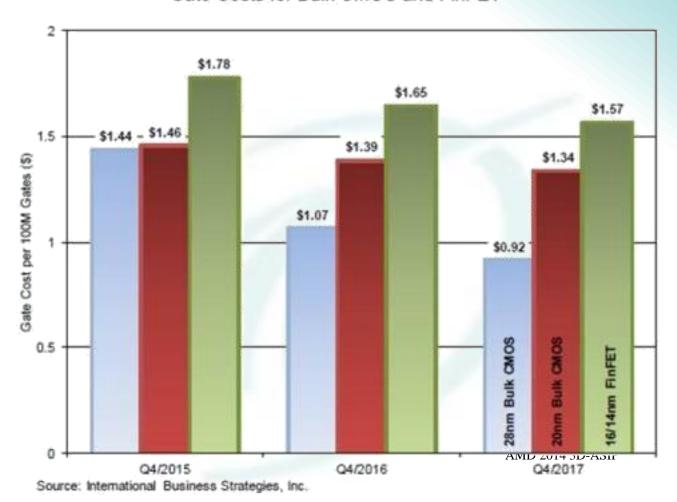
# **Expiring Economics**





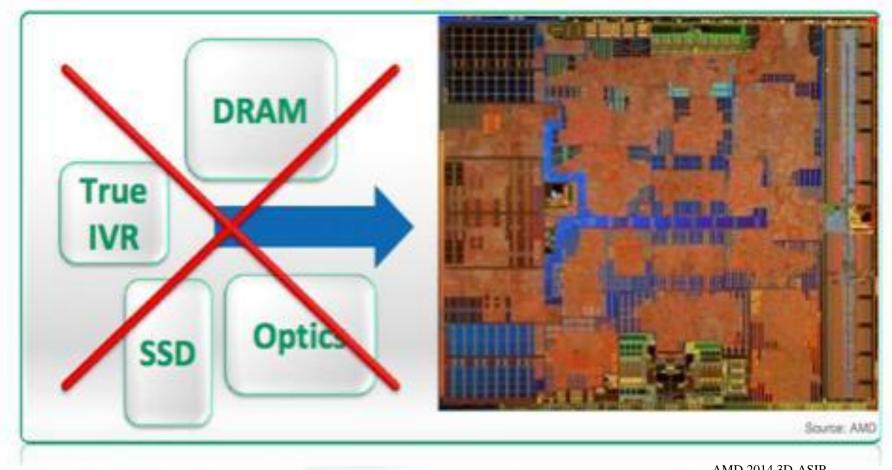
#### **Cost Trend Reversal**

#### Gate Costs for Bulk CMOS and FinFET





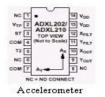
# The Apples & Oranges of SOC



AMD 2014 3D-ASIP



# Internet Of Things



















Gieger-Muller Radiation Sensor









Pyroelectric Detector

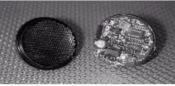


















Touch Switch Mechanical Tilt Sensors

Pressure Switch

Miniature Polaroid Sensor



Sensor

Remote Receiver









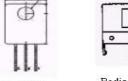


IRDA Transceiver



Hall Effect Magnetic Field Sensors







Remote Receiver

IR Amplifier Sensor









Compass





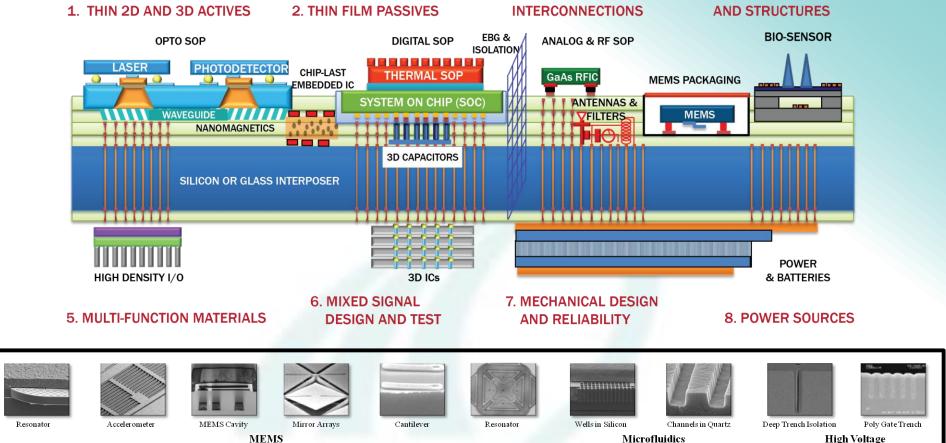
Piezo Ultrasonic Transducers



#### More Than Moore

#### GEORGIA TECH PRC

4. THERMAL INTERFACES



3. SYSTEM



**SEMICONDUCTOR** 

Microfluidics

**High Voltage** 



#### **MORE THAN MOORE**

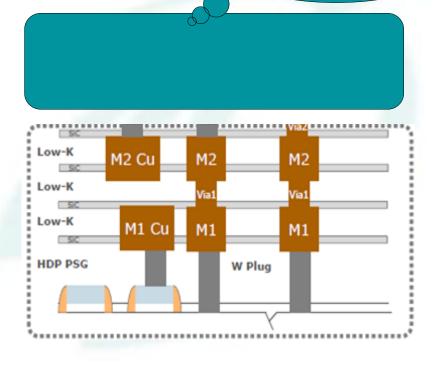


#### The Fabrication Road to More Than Moore

Memories, CMOS, Photonics, III-V, Novel Materials, Microfluidics, MEMS, etc.

Build novel structures BEOL

Start with FEOL CMOS wafer





#### Integration Paths: Additive Silicon and 2.5/3D

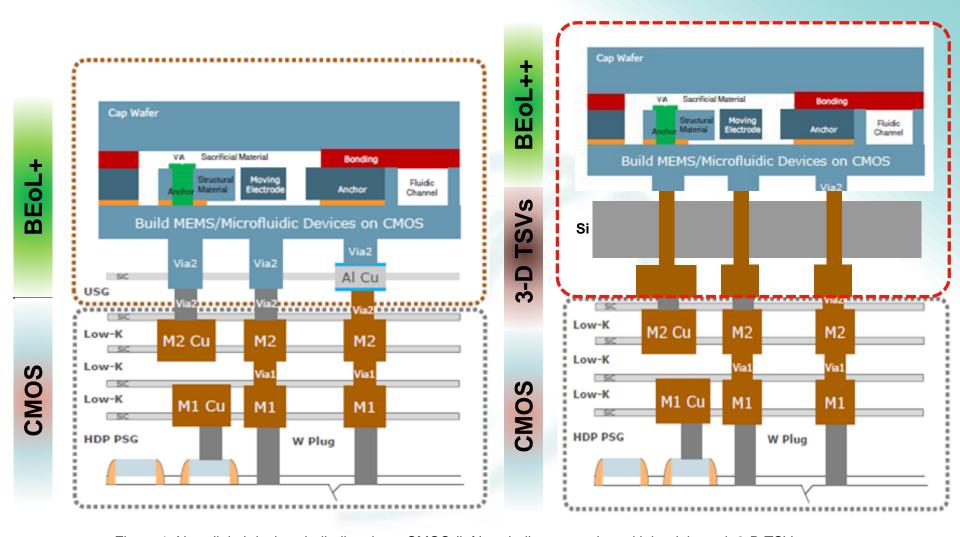
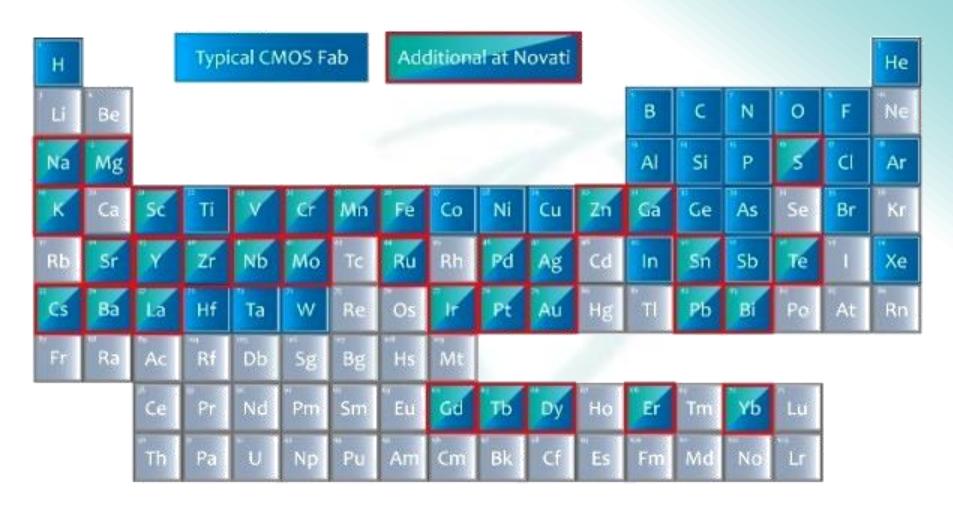


Figure 1: Non-digital devices built directly on CMOS (left), or built separately and joined through 3-D TSVs

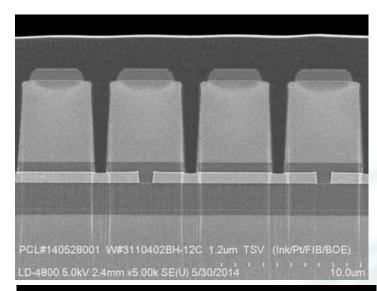


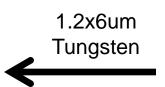
#### New Elements Introduced to Fabrication

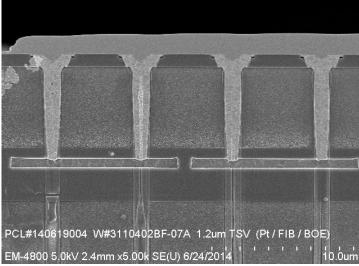




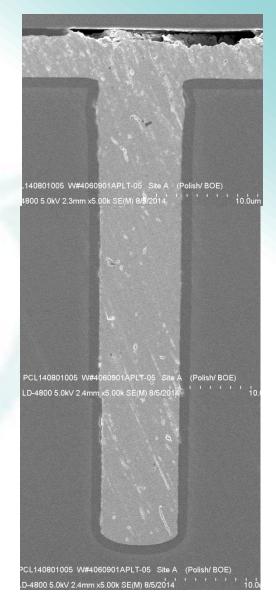
#### TSV Insertion to Create 2.5/3D Assemblies





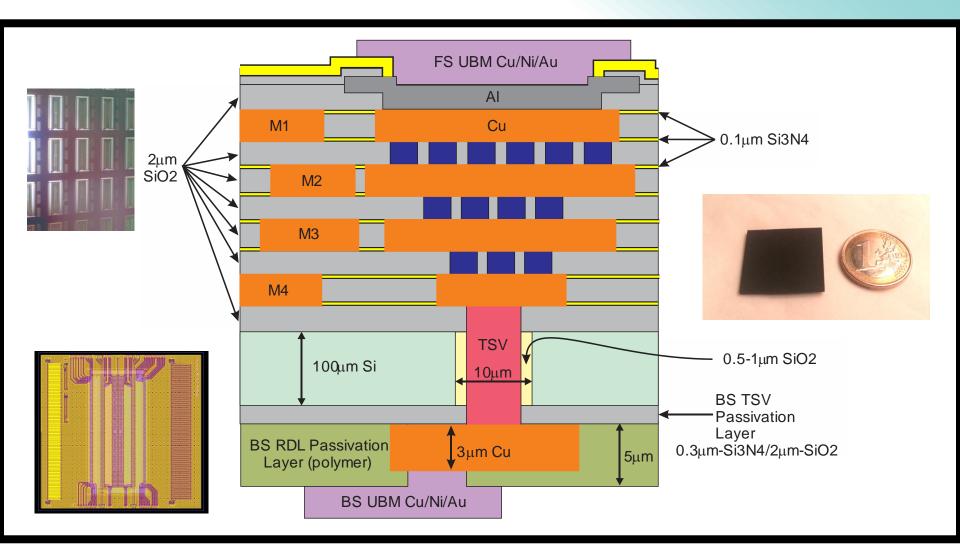


10x100um Copper



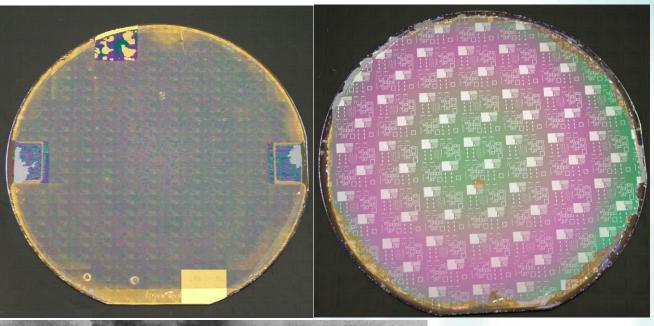


# Si Interposers

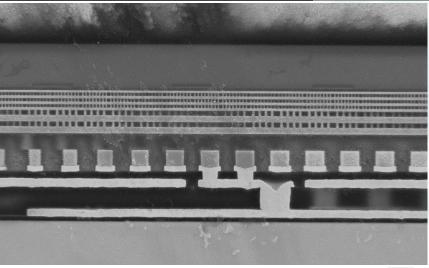


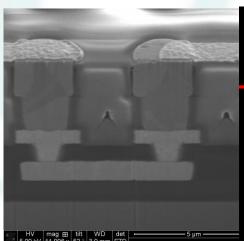


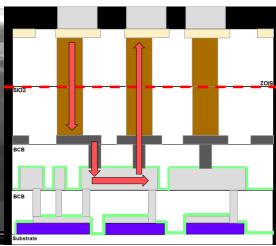
#### Mixed CMOS-3/5 100mm InP/CMOS



- GaN
- 3D CMOS/InP/GaN
- GaAs
- Graphene









Advanced 3D Cooling

View from outlet side

Aluminum plate

Coolant In

Gas Bypass Cut

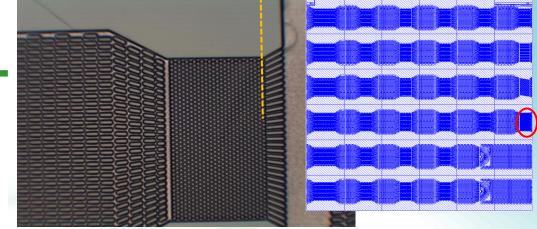
Chip Seal Girdle Gasket

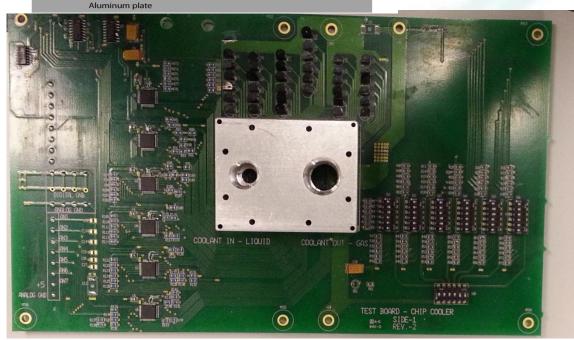
View from side

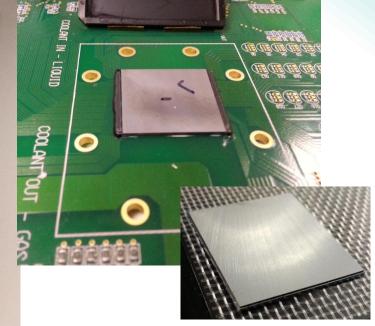
Metal/Lexan

Liquid Manifold

Cover

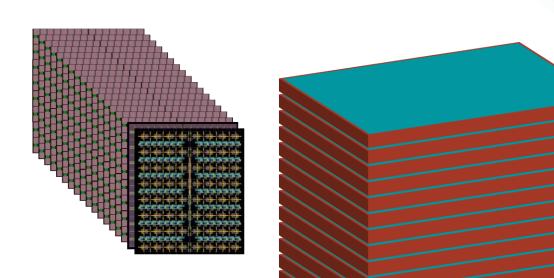








## DiRAM4 "Dis-Integrated" 3D Memory



DRAM layers 4xnm node

2 million vertical connections per lay per die

I/O layer contains: I/O, interface logic and — R&R control CPU.

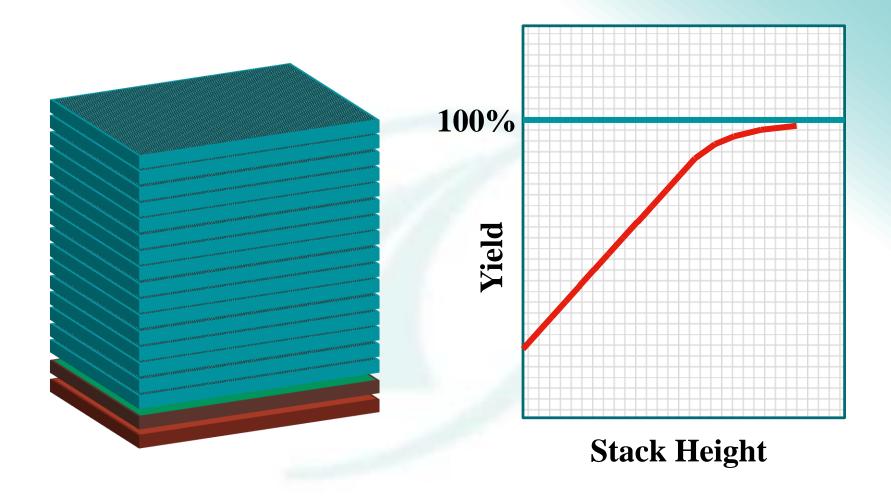
65nm node

Better yielding than 2D equivalent!

Controller layer contains: sense amps, CAMs, row/column decodes and test engines. 40nm node

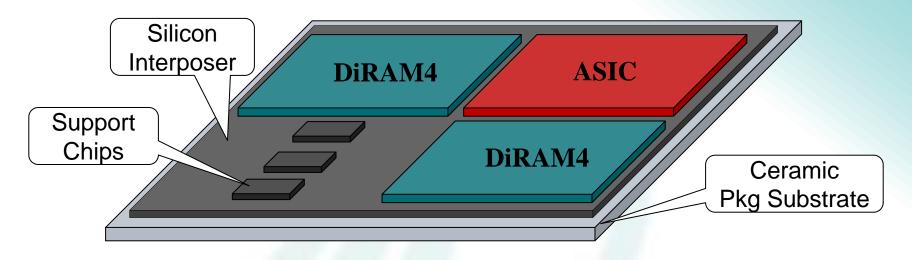


# Bi-STAR Repair Improves Yield





#### **HPC Processor Modules**



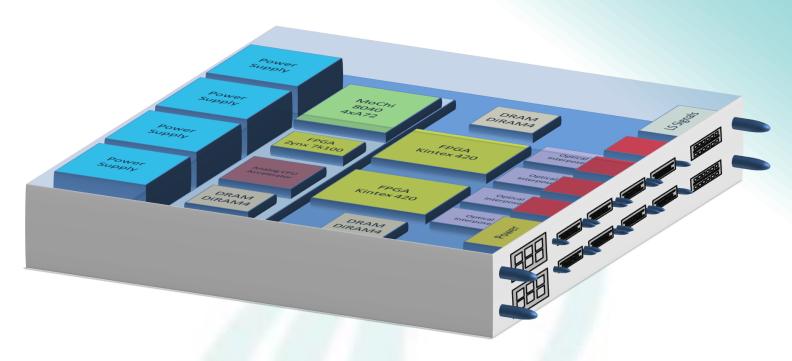
#### Si Interposer-based Ceramic Package

e.g. DiRAM4 plus Custom Processor

50 μ - 100 μ pitch Copper Pillar Die-to-Interposer-to-Die Interconnect
~ 10000 Connections – Mostly die-to-die inside package
~250 μ pitch C4 Bump Interposer-to-Ceramic Package Substrate Interconnect
~ 2000 Connections – Lots of replicated power connections
1 mm pitch Solder Bump Package Substrate-to-Customer PCB Interconnect
Several Hundred of Connections



# And Full Subsystem Modules

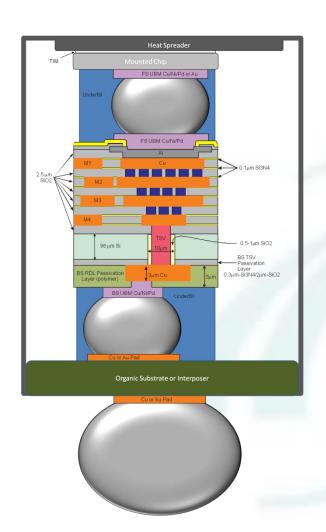


#### **System Modules**

Multiple Packages and /or Die on High Performance Organic Interposer/Substrate with System Connectors (Electrical: Card edge or Plugs, Optical: Fiber-optic Cable connectors)



## **Supply Chain**



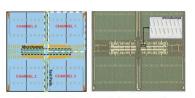
Donor Die Donor Die Bump Interposer UBM Topside Interposer Interposer UBM Bottomside Interposer Bump Interposer Underfill Donor Die Underfill Organic Substrate Substrate Bump TIM Package Lid Carrier Wafer Singulation Bond/Debond





# 2.5/3D CHANGE IS HERE





#### The Semiconductor Revolution

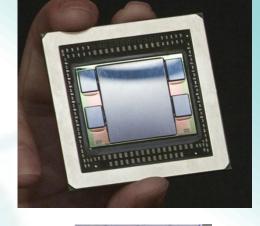


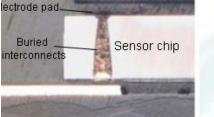
16Gb NAND flash (2Gx8 chips), Wide Bus DRAM, VNAND

> Hynix HBM DRAM

#### Intel

CPU + memory

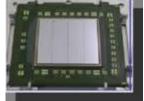




Cover glass

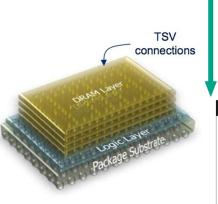
560µ

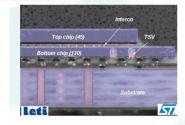
Sony CMOS Sensor



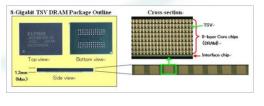


4 die 65nm interposer





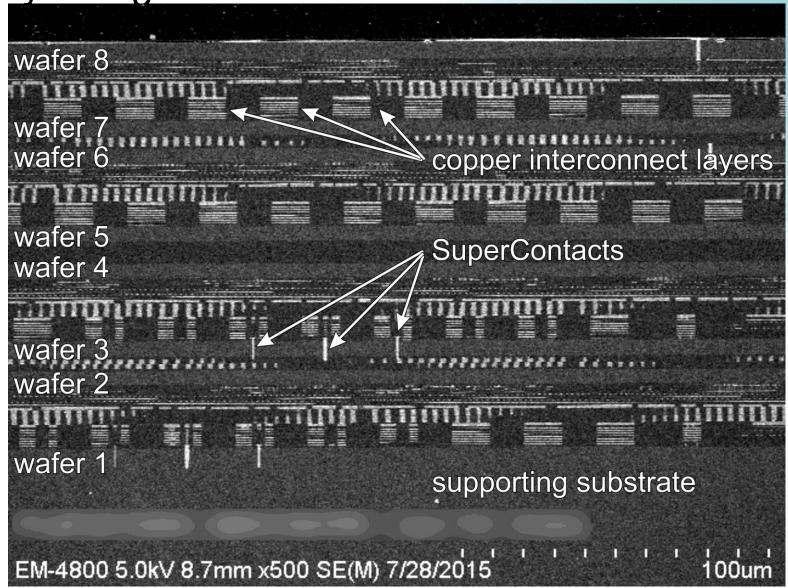
AMD Radon R9



#### **IBM**

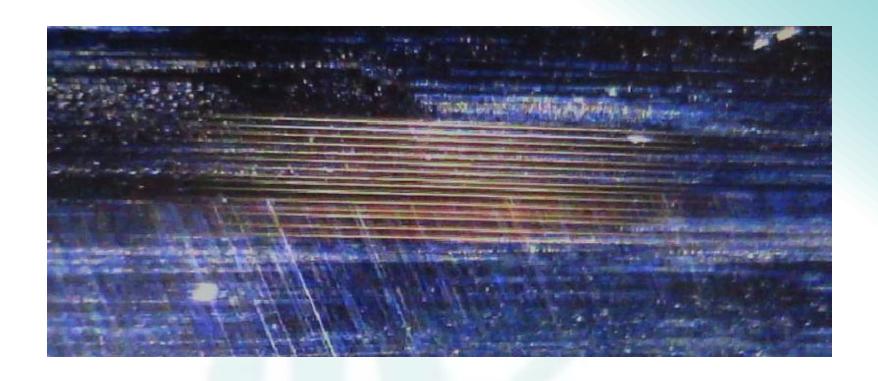
RF Silicon Circuit Board / TSV Logic & Analog

Toshiba 3D NAND 8 Layer Logic Stack





# 16 Layer Mechanical Device Stack





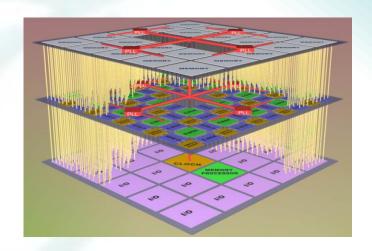
# Bonding in Action





#### Summary

- 2.5/3D market is in the adoption cycle
  - Moving from novelty to mainstream
- Drivers are:
  - Heterogeneous integration
  - SWaP
  - Increasing performance
  - Lower <u>system</u> costs
- First markets are:
  - Logic Memory
  - Sensors
- Significant industry shifts will happen
  - Silicon circuit cards with "Lego" blocks





## **Austin Facility Overview**

- 110 Employees: 90 in Ops and Engineering
- Over 150 production grade tools
- 68,000 sq ft Class 10 clean room
- 24/7 operations & maintenance
- Manufacturing Execution Systems (MES)
- IP secure environments, robust quality systems
- ISO certified/ITAR registered
- Full-flow 200mm silicon processing, 300mm back-end (Copper/Low-k)
- Process library with > 25000 recipes
- Novel materials (ALD, PZT, III-V, etc)
- Copper & Aluminum BEOL
- Contact through 193nm & IR lithography
- Silicon, SOI and Transparent MEMS substrates
- Electrical Characterization and Bench Test Lab
- Onsite analytical tools and labs: SIMS, SEM, TEM, Auger, VPD, ICP-MS, etc

